MOSFETs Silicon P-Channel MOS (U-MOSVI)

SSM3J76MFV

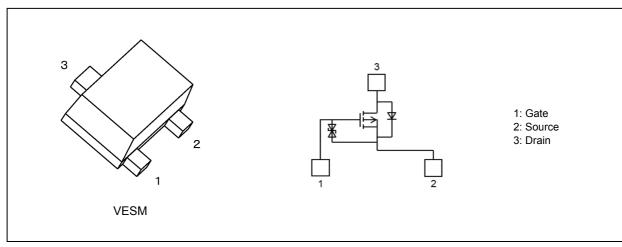
1. Applications

High-Speed Switching

2. Features

- (1) 1.2 V drive
- (2) Low drain-source on-resistance
 - $\begin{array}{l} : {\rm R}_{\rm DS(ON)} = 390 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.5 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 480 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -2.5 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 660 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -1.8 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 900 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -1.5 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 4000 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -1.2 \ {\rm V}) \end{array}$
- (3) Low leakage current

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

Char	acteristics	Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	-20	V
Gate-source voltage			V _{GSS}	±8	
Drain current (DC)		(Note 1)	Ι _D	-800	mA
Drain current (pulsed)		(Note 1)	I _{DP}	-1600]
Power dissipation		(Note 2)	PD	150	mW
Power dissipation		(Note 3)		500	mW
Power dissipation	(t<5s)	(Note 3)		800]
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on a 25.4 mm \times 25.4 mm \times 1.6 mm FR4 glass epoxy board (Cu pad: 0.585 mm²)

Note 3: Device mounted on a 25.4 mm \times 25.4 mm \times 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V_{GS} = ±5 V, V_{DS} = 0 V	_	—	±0.08	μA
			V_{GS} = ±8 V, V_{DS} = 0 V	—		±1	
Drain cut-off current		I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	_		-0.08	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = -1 mA, V _{GS} = 0 V	-20		_	V
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I _D = -1 mA, V _{GS} = 5 V	-15	_	—	
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = -3 V, I _D = -1 mA	-0.3	_	-1.0	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	$I_{\rm D}$ = -800 mA, $V_{\rm GS}$ = -4.5 V	_	310	390	mΩ
			$I_{\rm D}$ = -500 mA, $V_{\rm GS}$ = -2.5 V	—	380	480	
			$I_{\rm D}$ = -200 mA, $V_{\rm GS}$ = -1.8 V	_	470	660	
			$I_{\rm D}$ = -100 mA, $V_{\rm GS}$ = -1.5 V	_	560	900	
			I _D = -10 mA, V _{GS} = -1.2 V	—	770	4000	
Forward transfer admittance	(Note 3)	Y _{fs}	V _{DS} = -3 V, I _D = -100 mA	0.5	1.0	_	S

Note 1: If a forward bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

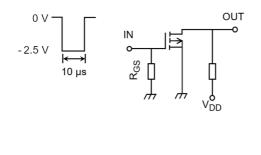
Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$. Take this into consideration when using the device.

Note 3: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V,	_	100	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	10	—	
Output capacitance	C _{oss}		_	16	—	
Switching time (turn-on time)	t _{on}	V _{DD} = -10 V, I _D = -200 mA V _{GS} = 0 to -2.5 V, R _{GS} = 50 Ω		8	—	ns
Switching time (turn-off time)	t _{off}	Duty \leq 1 %, V _{IN} : t _r , t _f < 5 ns, Common source, See Chapter 5.3.	_	26	—	

5.3. Switching Time Test Circuit



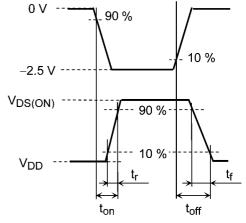


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V_{DD} = -10 V, V_{GS} = -4.5 V,	_	1.6		nC
Gate-source charge 1	Q _{gs1}	I _D = -800 mA	_	0.2		
Gate-drain charge	Q _{gd}		_	0.4	_	

5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	$I_{\rm D}$ = 800 mA, $V_{\rm GS}$ = 0 V	_	0.9	1.2	V

Note 1: Pulse measurement.

6. Marking

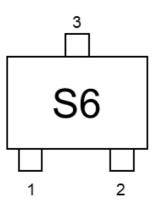
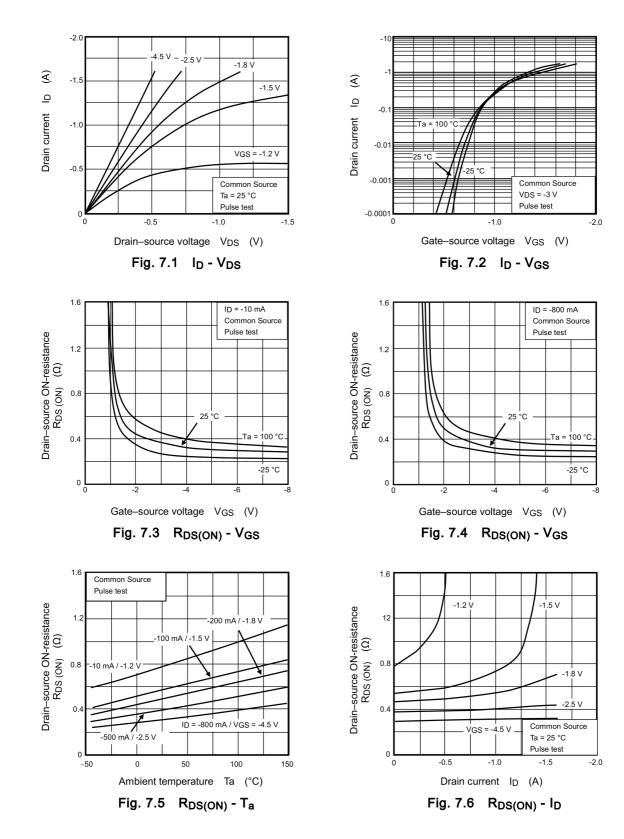


Fig. 6.1 Marking

7. Characteristics Curves (Note)



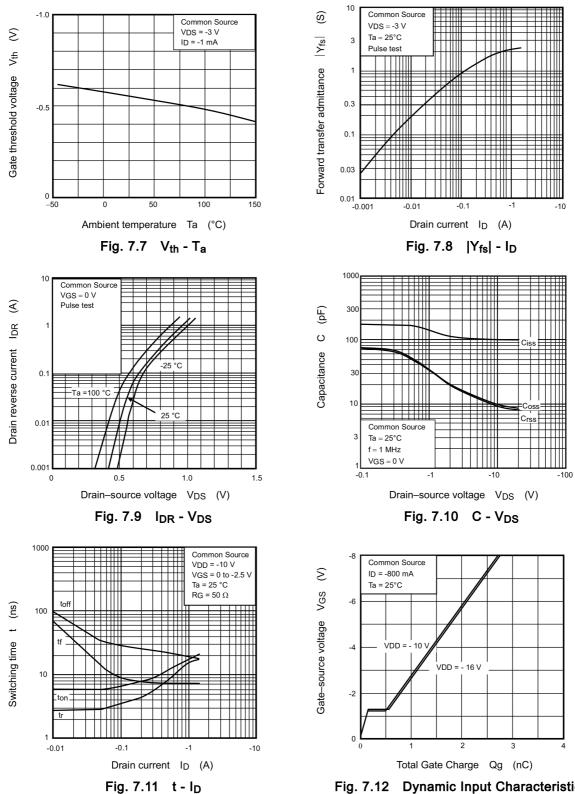
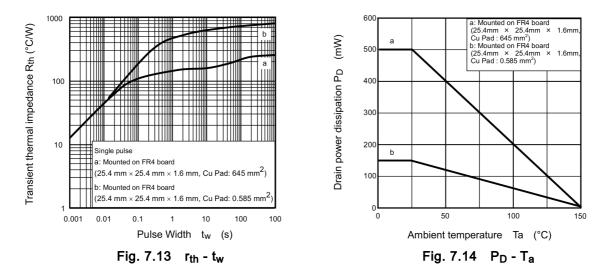


Fig. 7.12 Dynamic Input Characteristics





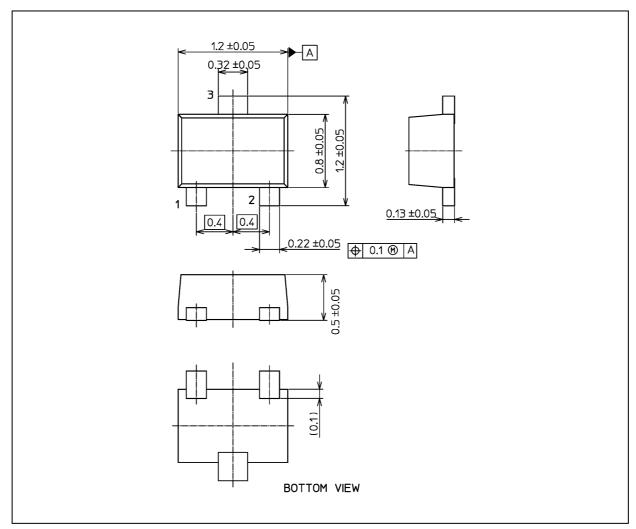
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



SSM3J76MFV

Package Dimensions

Unit: mm



Weight: 1.5 mg (typ.)

	Package Name(s)
JEDEC: SOT-723	
Nickname: VESM	

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